

FEATURES

- 10.2kV Isolation Package
- Low Reverse Recovery Charge
- High Switching Speed
- Low Forward Volt Drop
- Isolated AISiC Base With AlN Substrates
- Triple Diodes Can Be Paralleled For 3600A Rating

APPLICATIONS

- Chopper Diodes
- Boost and Buck Converters
- Free-wheel Circuits
- Snubber Circuit
- Resonant Converters
- Induction Heating
- Multi-level Switch Inverters

The DFM1200AXM45-TS000 is a triple 4500V, fast recovery diode (FRD) module. Designed for low power loss, the module is suitable for a variety of high voltage applications in motor drives and power conversion.

Fast switching times and low reverse recovery losses allow high frequency operation, making the device suitable for the latest drive designs employing PWM and high frequency switching.

The module incorporates an electrically isolated base plate and low inductance construction enabling circuit designers to optimise circuit layouts and utilise grounded heat sinks for safety.

ORDERING INFORMATION

Order As:

DFM1200AXM45-TS000

Note: When ordering, please use the complete part number

KEY PARAMETERS

V_{RRM}		4500V
V_F	(typ)	2.8V
I_F	(max)	1200A
I_{FM}	(max)	2400A

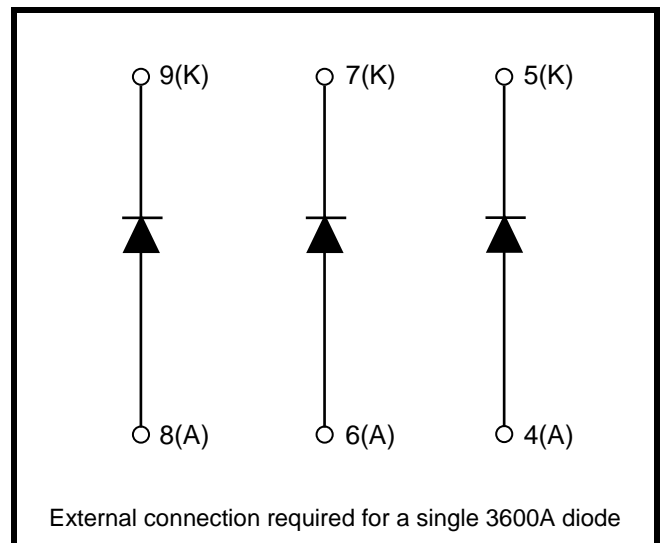


Fig. 1 Circuit configuration



Fig. 2 Package

ABSOLUTE MAXIMUM RATINGS

Stresses above those listed under 'Absolute Maximum Ratings' may cause permanent damage to the device. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture of the package. Appropriate safety precautions should always be followed. Exposure to Absolute Maximum Ratings may affect device reliability.

$T_{\text{case}} = 25^{\circ}\text{C}$ unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
V_{RRM}	Repetitive peak reverse voltage	$T_j = 125^{\circ}\text{C}$	4500	V
I_{F}	Forward current (per arm)	DC, $T_{\text{case}} = 65^{\circ}\text{C}$	1200	A
I_{FM}	Max. forward current	$T_{\text{case}} = 115^{\circ}\text{C}$, $t_p = 1\text{ms}$	2400	A
I^2t	I^2t value fuse current rating	$V_R = 0$, $t_p = 10\text{ms}$, $T_j = 125^{\circ}\text{C}$	460	kA^2s
P_{max}	Max. power dissipation	$T_{\text{case}} = 25^{\circ}\text{C}$, $T_j = 125^{\circ}\text{C}$	6250	W
V_{isol}	Isolation voltage – per module	Commoned terminals to base plate. AC RMS, 1 min, 50Hz	10.2	kV
Q_{PD}	Partial discharge – per module	IEC1287, $V_1 = 6900\text{V}$, $V_2 = 5100\text{V}$, 50Hz RMS	10	pC

THERMAL AND MECHANICAL RATINGS

Internal insulation material:	AlN
Baseplate material:	AlSiC
Creepage distance:	56mm
Clearance:	26mm
CTI (Comparative Tracking Index):	> 600

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
$R_{\text{th}(j-c)}$	Thermal resistance (per arm)	Continuous dissipation – junction to case	-	-	16	$^{\circ}\text{C}/\text{kW}$
$R_{\text{th}(c-h)}$	Thermal resistance – case to heatsink (per module)	Mounting torque 5Nm (with mounting grease)	-	-	8	$^{\circ}\text{C}/\text{kW}$
T_j	Junction temperature		-40	-	125	$^{\circ}\text{C}$
T_{stg}	Storage temperature range		-40	-	125	$^{\circ}\text{C}$
	Screw Torque	Mounting – M6	-	-	5	Nm
		Electrical connections – M8	-	-	10	Nm

STATIC ELECTRICAL CHARACTERISTICS – PER ARM

$T_{\text{case}} = 25^{\circ}\text{C}$ unless stated otherwise.

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
I_{RM}	Peak reverse current	$V_{\text{R}} = 4500\text{V}$, $T_{\text{j}} = 125^{\circ}\text{C}$			90	mA
V_{F}	Forward voltage	$I_{\text{F}} = 1200\text{A}$		2.8		V
		$I_{\text{F}} = 1200\text{A}$, $T_{\text{j}} = 125^{\circ}\text{C}$		3.2		V
L_{M}	Inductance	-		40		nH

DYNAMIC ELECTRICAL CHARACTERISTICS – PER ARM

$T_{\text{case}} = 25^{\circ}\text{C}$ unless stated otherwise (when used with DIM1200ASM45-TS001)

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
Q_{rr}	Reverse recovery charge	$I_{\text{F}} = 1200\text{A}$ $V_{\text{R}} = 2800\text{V}$ $di_{\text{F}}/dt = 3000\text{A}/\mu\text{s}$		1340		μC
I_{rr}	Peak reverse recovery current			1030		A
E_{rec}	Reverse recovery energy			2200		mJ

$T_{\text{case}} = 125^{\circ}\text{C}$ unless stated otherwise (when used with DIM1200ASM45-TS001)

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
Q_{rr}	Reverse recovery charge	$I_{\text{F}} = 1200\text{A}$ $V_{\text{R}} = 2800\text{V}$ $di_{\text{F}}/dt = 3200\text{A}/\mu\text{s}$		2200		μC
I_{rr}	Peak reverse recovery current			1100		A
E_{rec}	Reverse recovery energy			3750		mJ

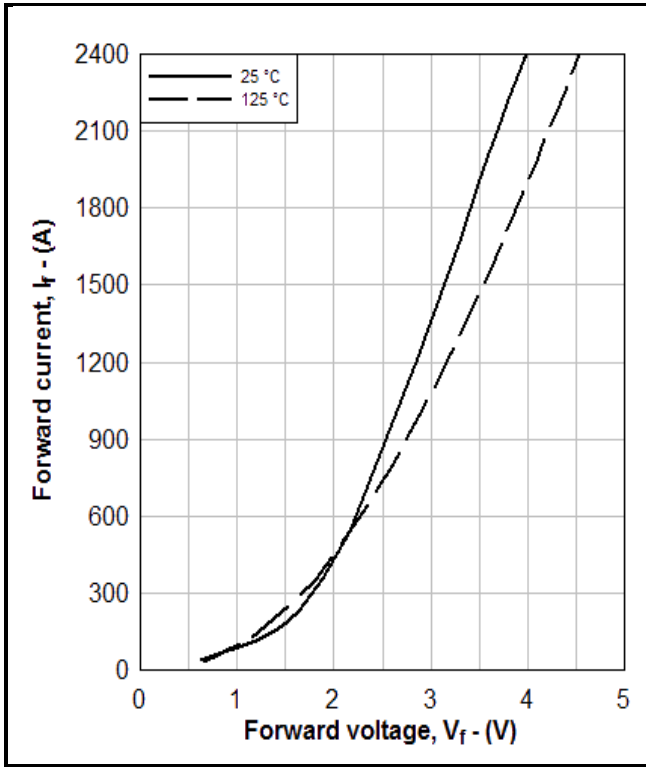


Fig. 3 Diode typical forward characteristics

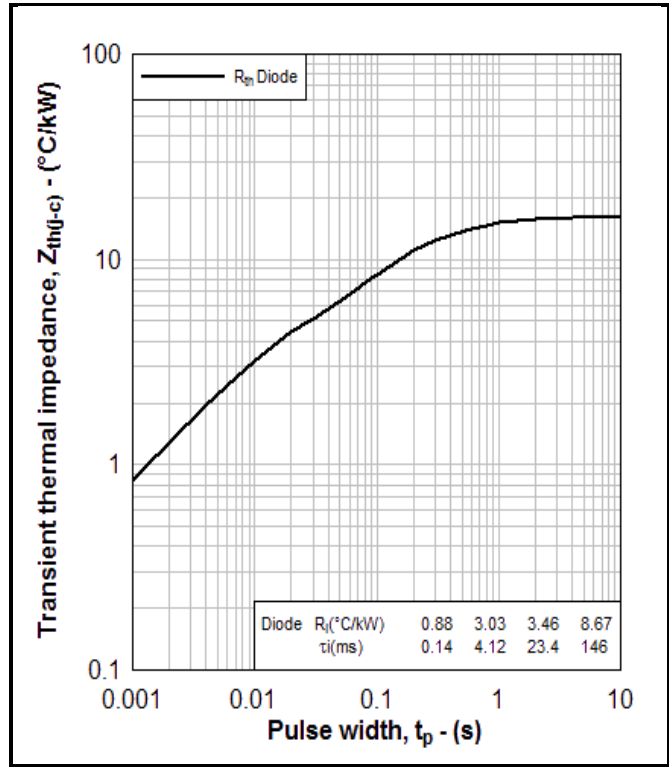


Fig. 4 Transient thermal impedance

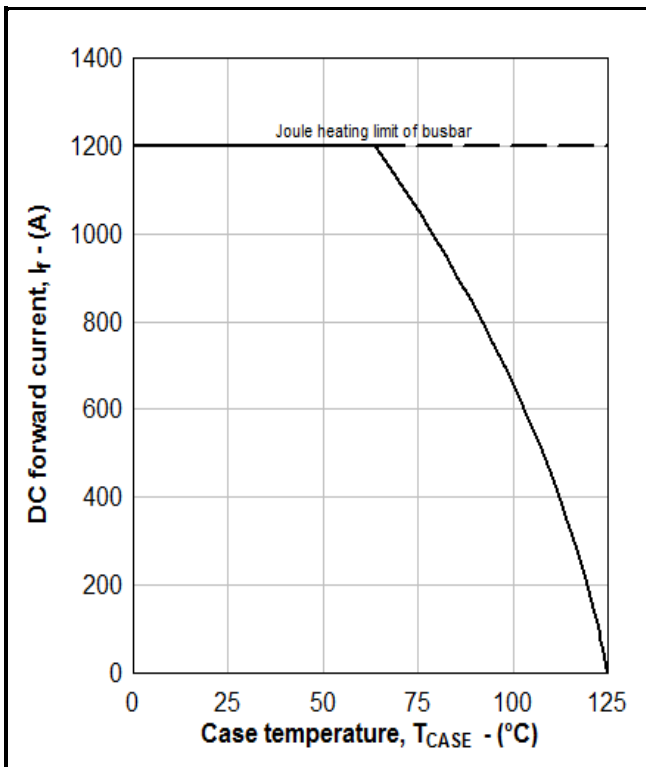


Fig. 5 DC current rating vs case temperature

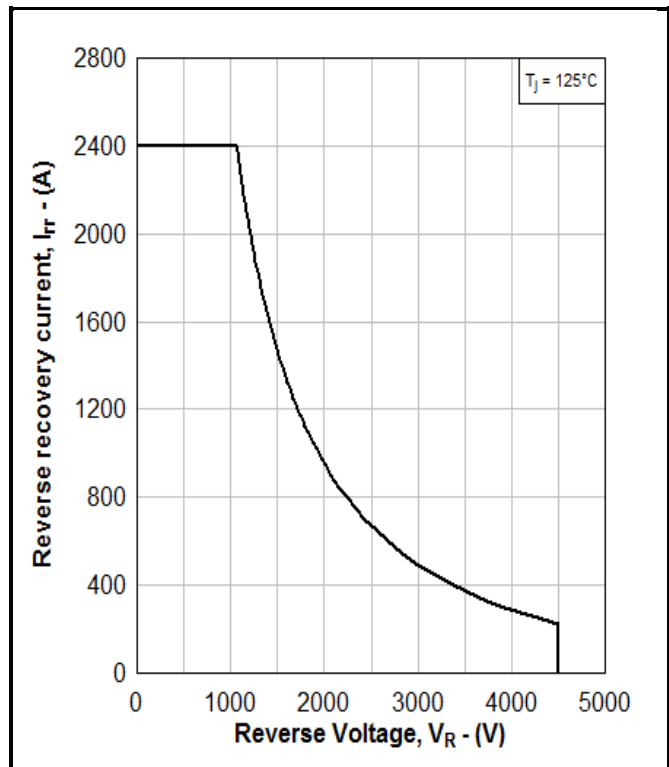


Fig. 6 Reverse Bias Safe Operating Area (RBSOA)

PACKAGE DETAILS

For further package information, please visit our website or contact Customer Services.
All dimensions in mm, unless stated otherwise.
DO NOT SCALE.

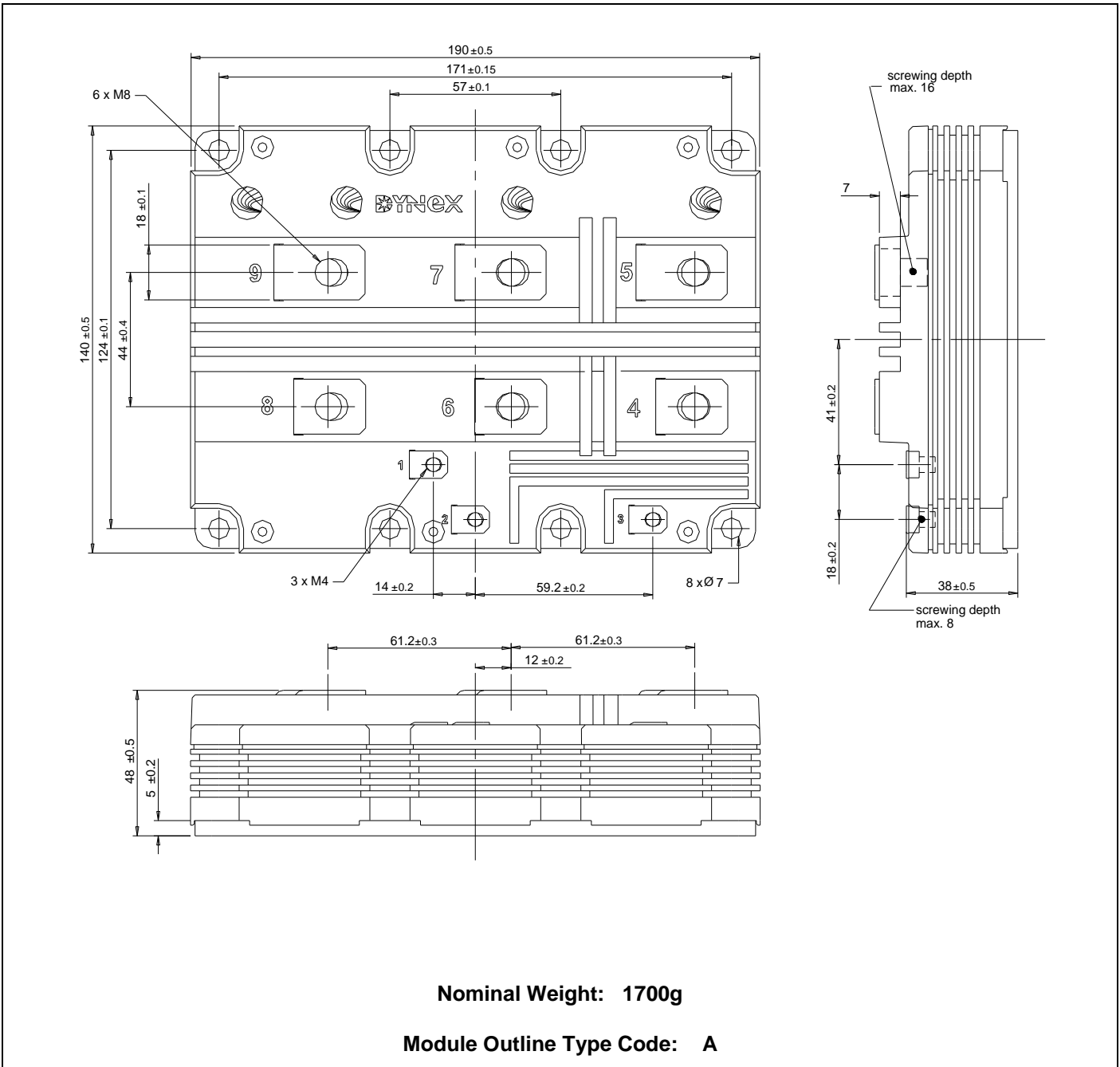


Fig. 7 Module outline drawing

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The products must not be touched when operating because there is a danger of electrocution or severe burning. Always use protective safety equipment such as appropriate shields for the product and wear safety glasses. Even when disconnected any electric charge remaining in the product must be discharged and allowed to cool before safe handling using protective gloves.

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HEADQUARTERS OPERATIONS

DYNEX SEMICONDUCTOR LTD

Doddington Road, Lincoln, Lincolnshire, LN6 3LF,
United Kingdom

Fax: +44(0)1522 500550

Tel: +44(0)1522 500500

Web: <http://www.dynexsemi.com>

CUSTOMER SERVICE

DYNEX SEMICONDUCTOR LTD

Doddington Road, Lincoln, Lincolnshire, LN6 3LF,
United Kingdom

Tel: +44(0)1522 502753 / 502901

Email: powersolutions@dynexsemi.com